TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

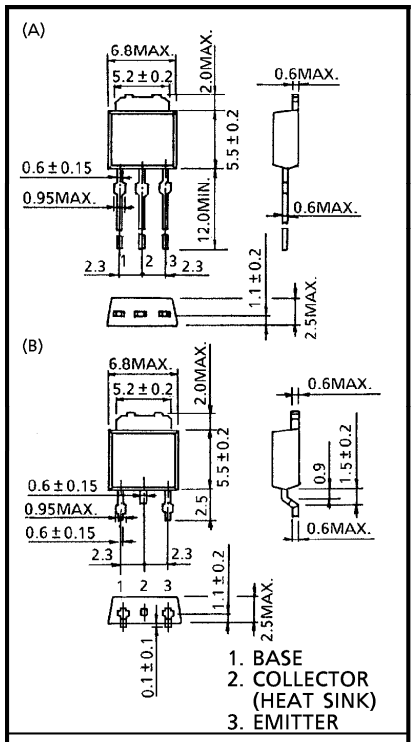
2SC3072

STROBE FLASH APPLICATIONS

MEDIUM POWER AMPLIFIER APPLICATIONS

- High DC Current Gain : h_{FE} = 140~450 (V_{CE} = 2 V, I_C = 0.5 A)
  h_{FE} = 70 (Min.) (V_{CE} = 2 V, I_C = 4 A)
- Low Collector Saturation Voltage
  : $V_{CE\ (sat)}$ = 1.0 V (Max.) (I_C = 4 A, I_B = 0.1 A)
- High Power Dissipation
  : P_C = 10 W (Tc = 25°C), P_C = 1.0 W (Ta = 25°C)

Unit in mm



JEDEC	—
EIAJ	—
TOSHIBA	(A) 2-7B1A (B) 2-7B2A

Weight : 0.36 g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	50	V
Collector-Emitter Voltage		V_{CES}	40	V
		V_{CEO}	20	
Emitter-Base Voltage		V_{EBO}	8	V
Collector Current	DC	I_C	5	A
	Pulsed (Note 1)	I_{CP}	8	A
Base Current		I_B	0.5	A
Collector Power Dissipation	Ta = 25°C	P_C	1.0	W
	Tc = 25°C		10	
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

Note 1 : Pulse Test : Pulse Width = 10 ms (Max.) Duty Cycle = 30% (Max.)

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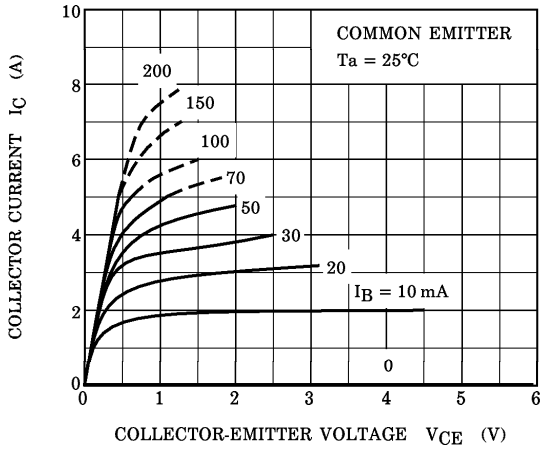
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

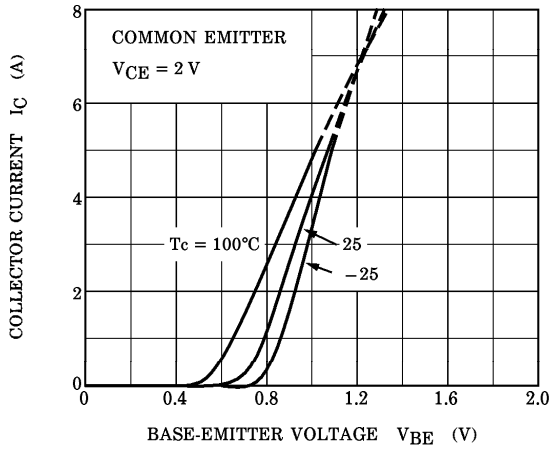
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB} = 40 V, I_E = 0	—	—	100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 8 V, I_C = 0	—	—	100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 10 mA, I_B = 0	20	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note 2)	V_{CE} = 2 V, I_C = 0.5 A	140	—	450	
	$h_{FE(2)}$	V_{CE} = 2 V, I_C = 4 A	70	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 4 A, I_B = 0.1 A	—	—	1.0	V
Base-Emitter Voltage	V_{BE}	V_{CE} = 2 V, I_C = 4 A	—	—	1.5	V
Transition Frequency	f_T	V_{CE} = 2 V, I_C = 0.5 A	—	100	—	MHz
Collector Output Capacitance	C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1 MHz	—	40	—	pF

Note 2 : $h_{FE(1)}$ Classification A : 140~240, B : 200~330, C : 300~450

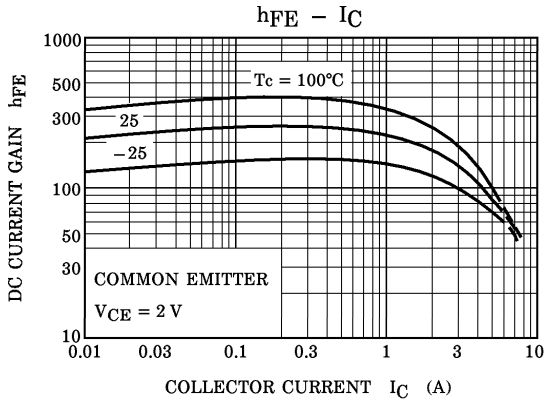
I_C – V_{CE}



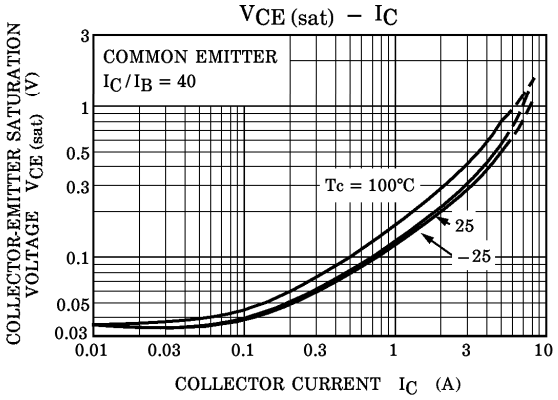
I_C – V_{BE}



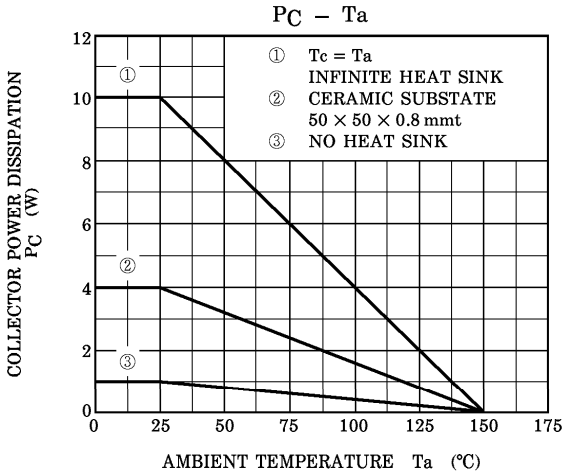
h_{FE} – I_C



$V_{CE\,(sat)}$ – I_C



P_C – Ta



SAFE OPERATING AREA

